

FIG. 1

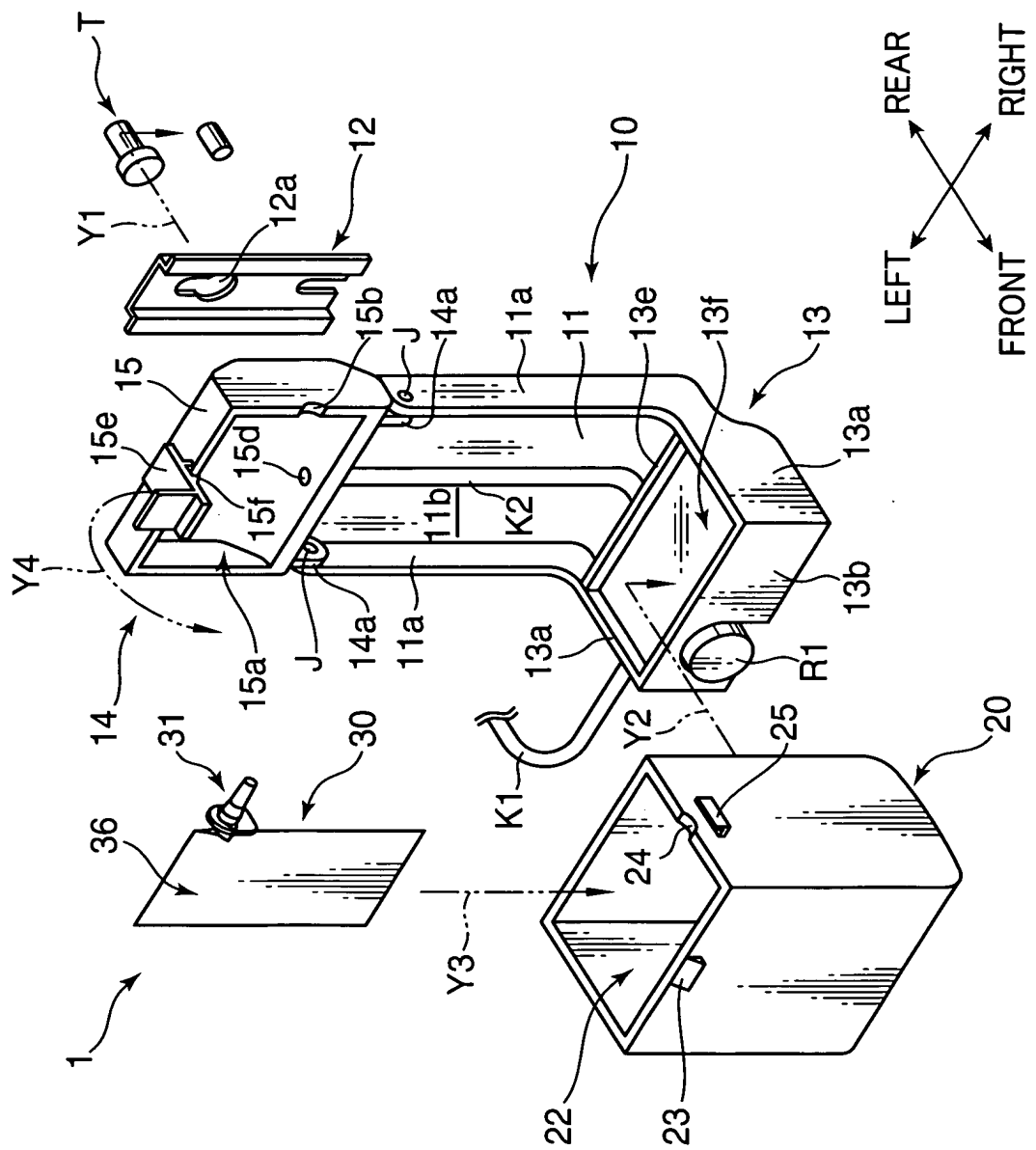


FIG. 2

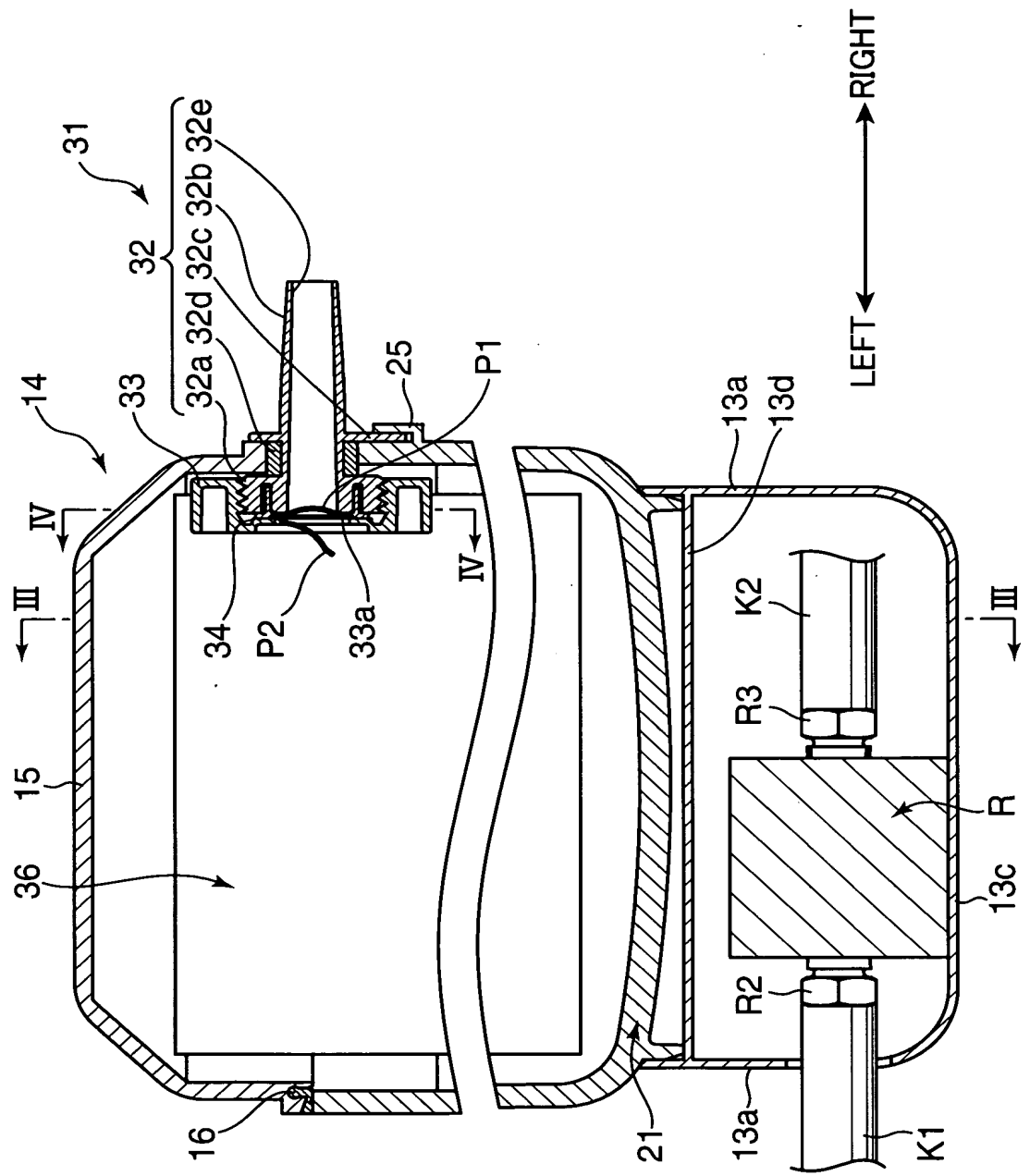


FIG. 3

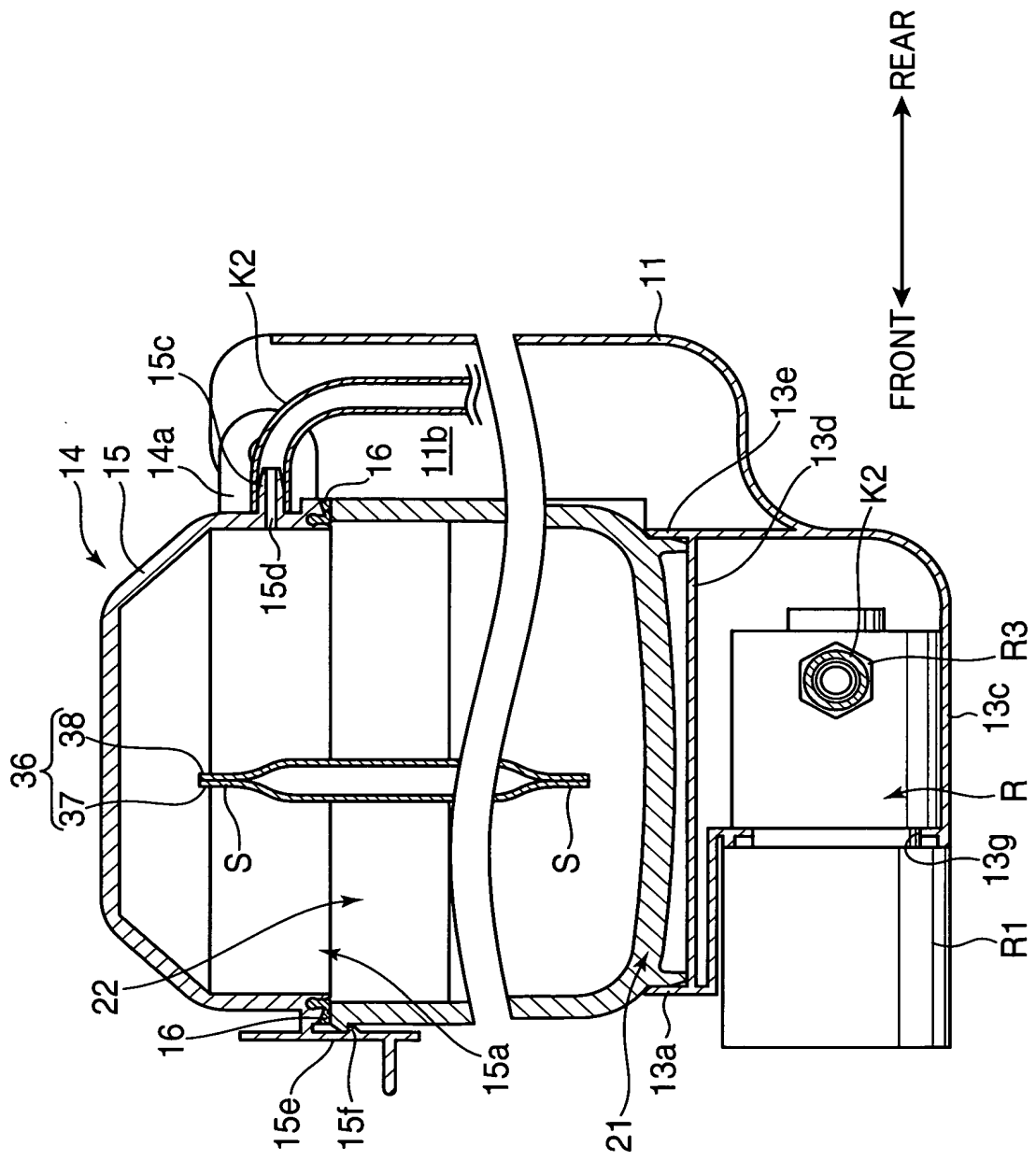


FIG. 4

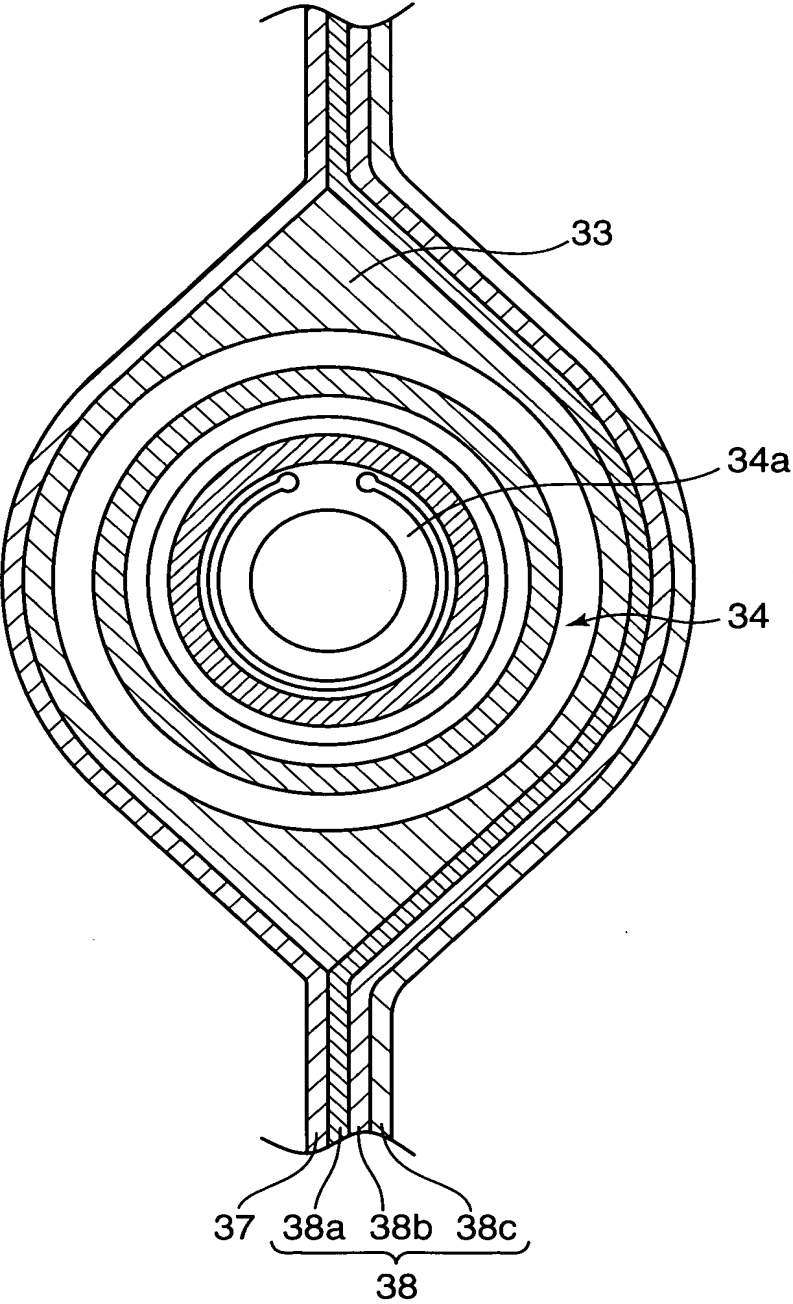


FIG. 5A

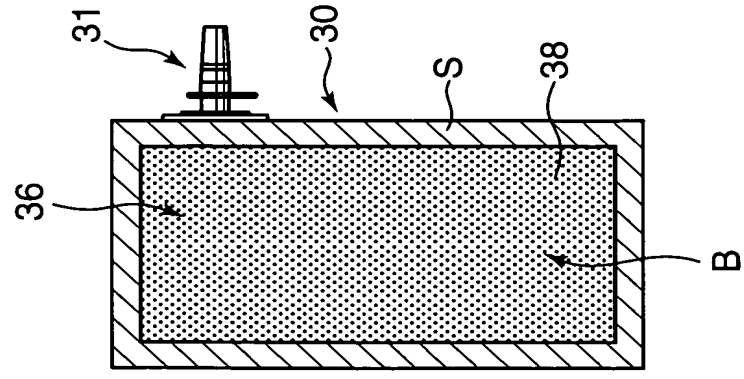


FIG. 5B

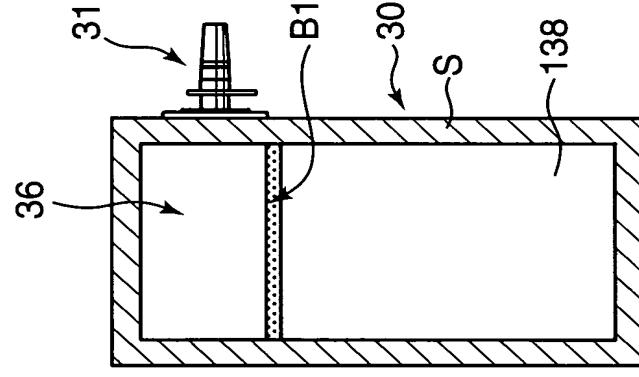


FIG. 5C

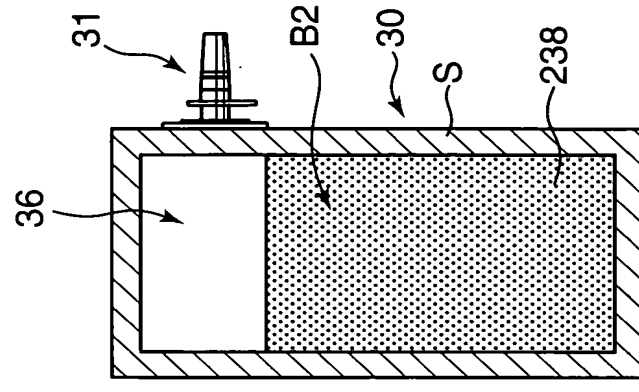


FIG. 6A

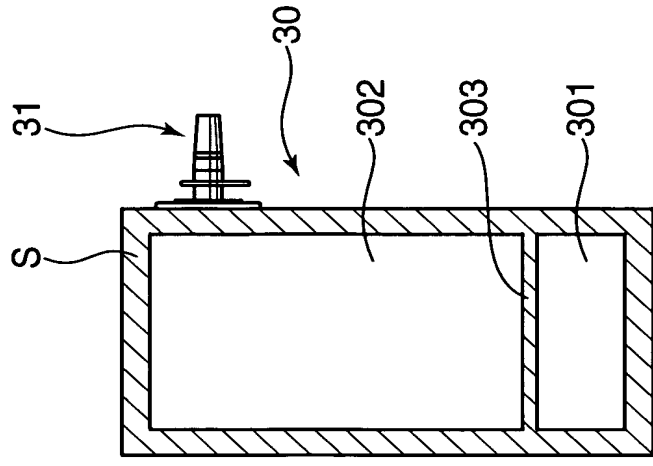


FIG. 6B

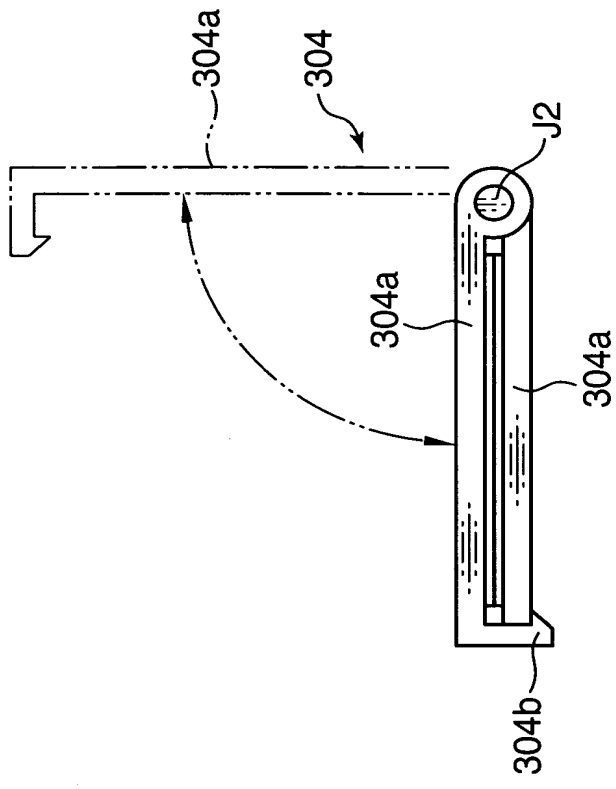


FIG. 7

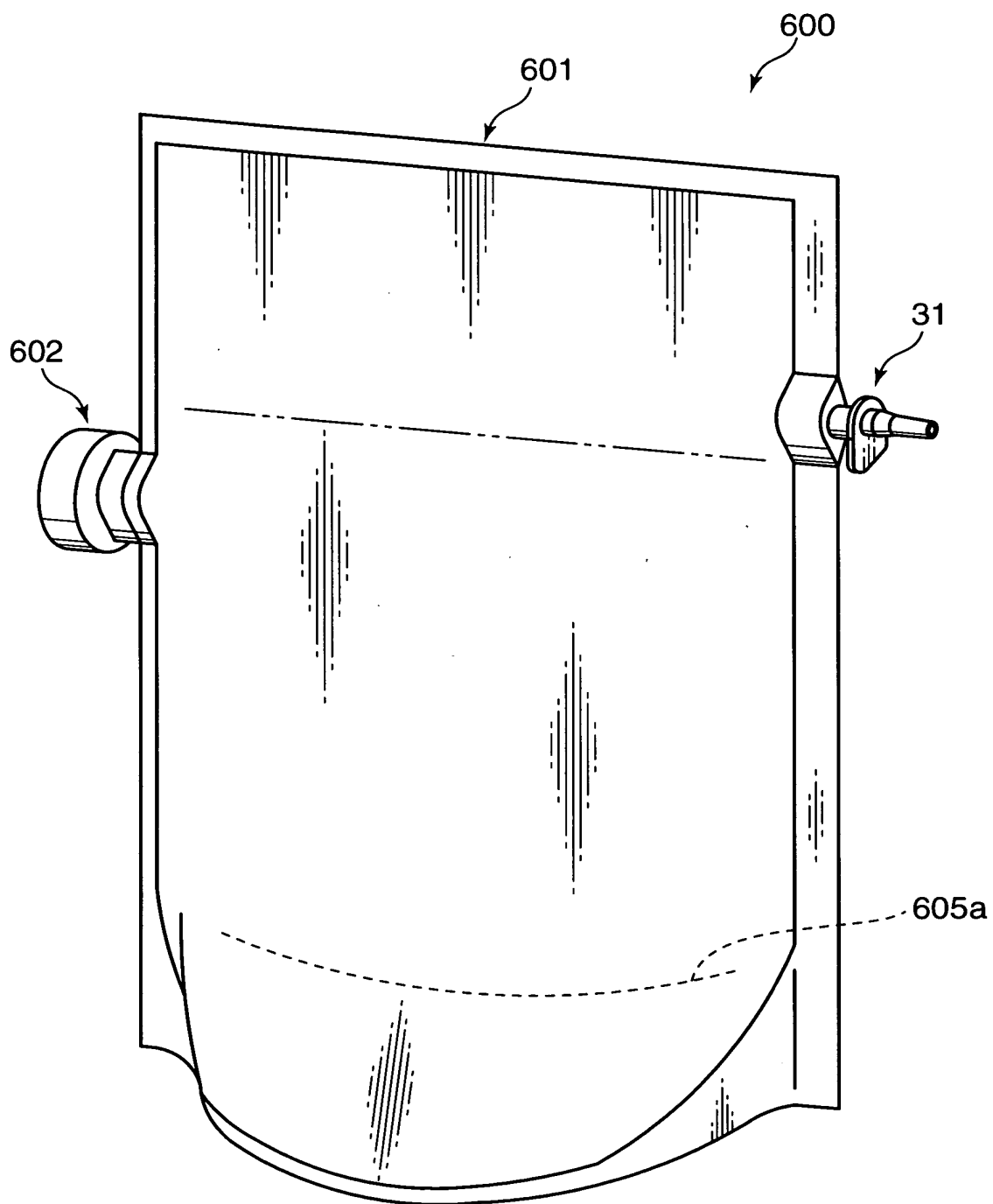


FIG. 8

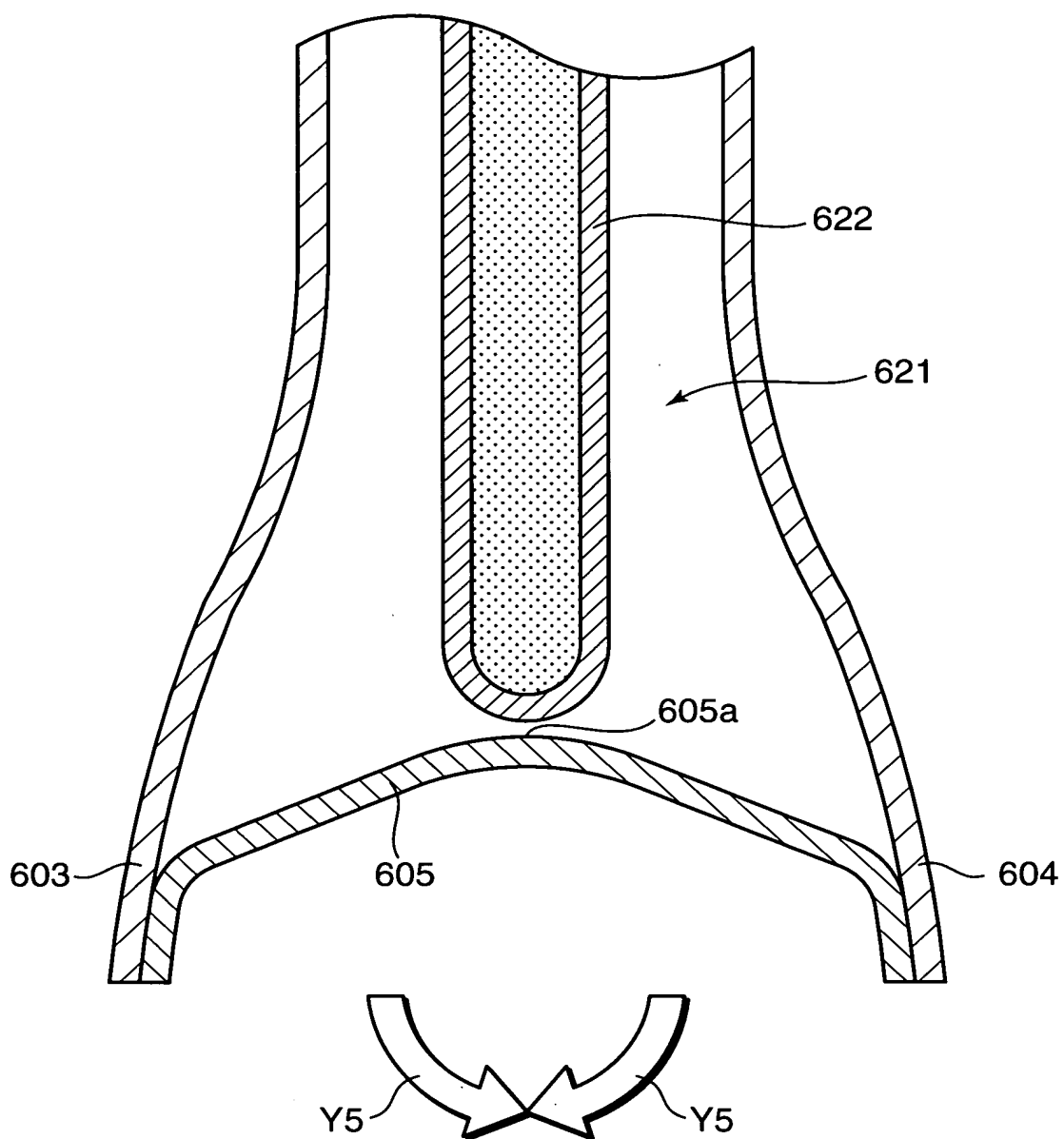


Figure 6 shows two cross-sectional views of a semiconductor device. The top view shows a device with a central channel 608, a gate stack 606, and a source/drain region 609. A cross-section Y6 is indicated. The bottom view shows a similar device with a cross-section Y7 indicated. Various layers and structures are labeled with reference numerals.

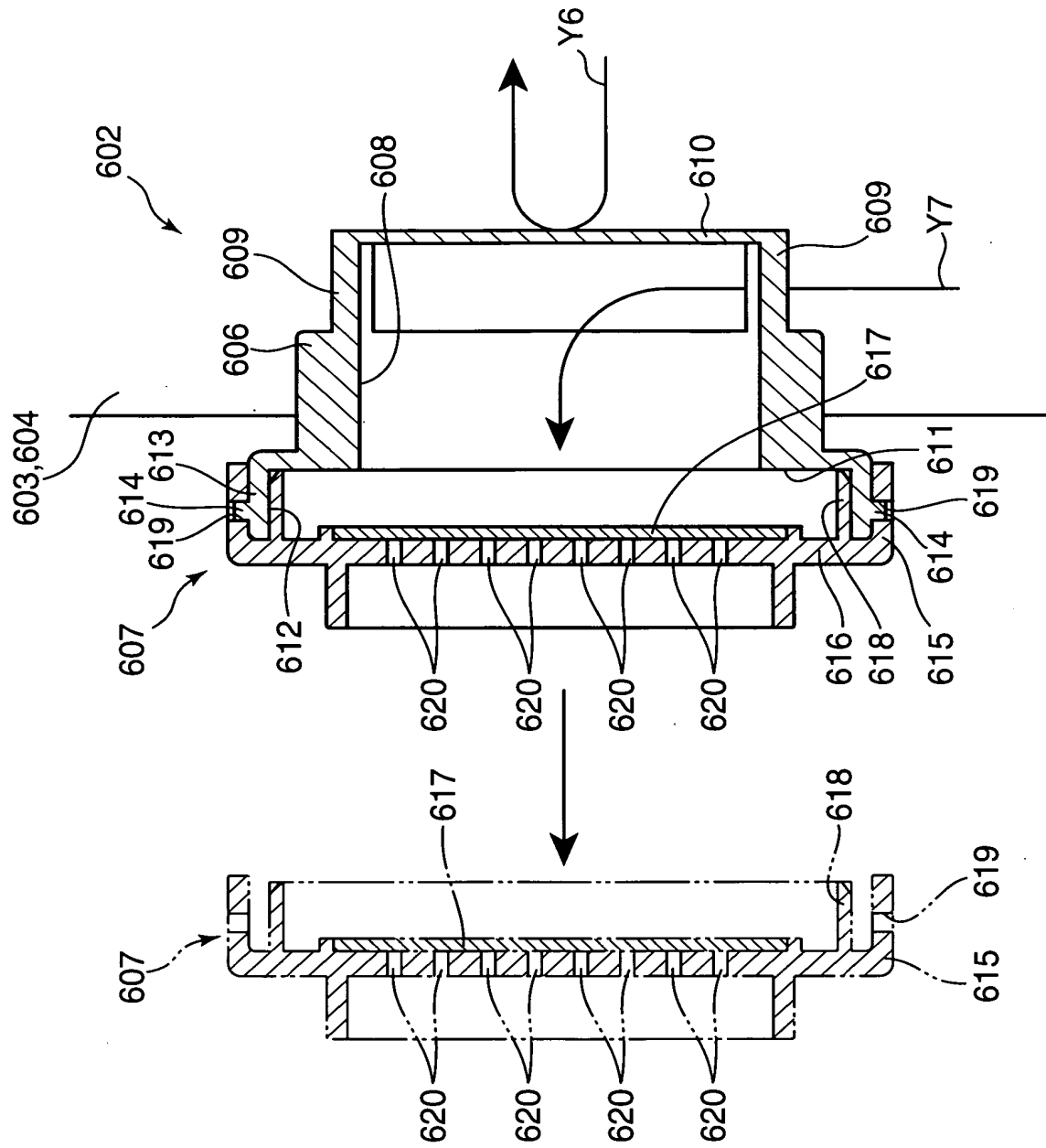


FIG. 10A

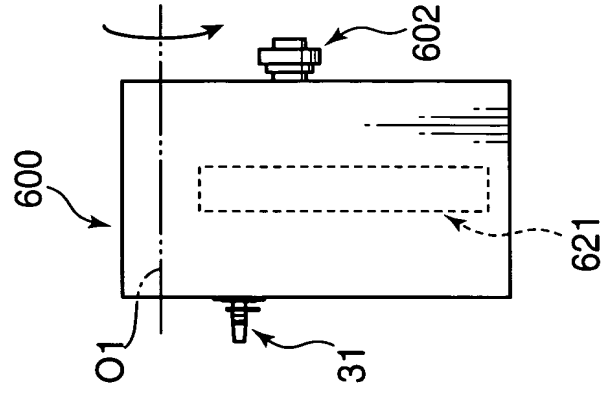


FIG. 10B

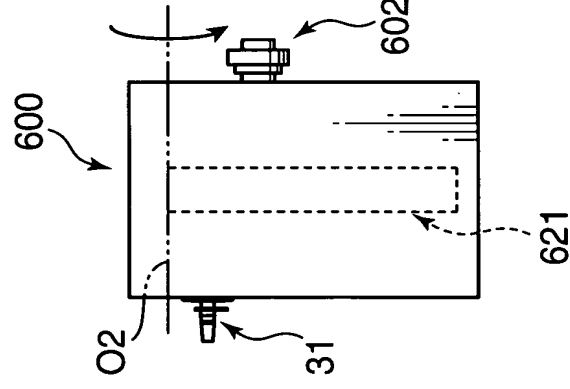


FIG. 10C

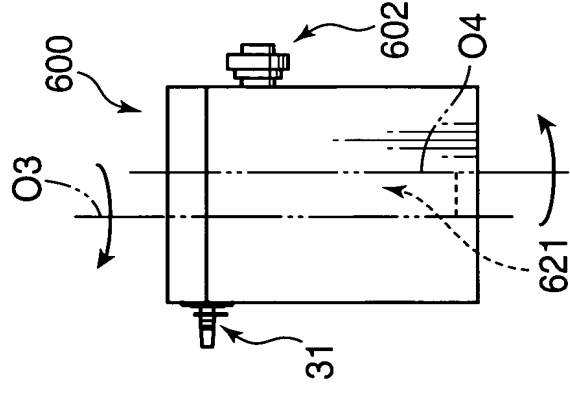


FIG. 10D

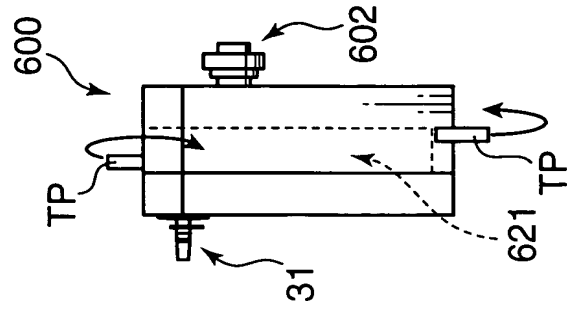


FIG. 11

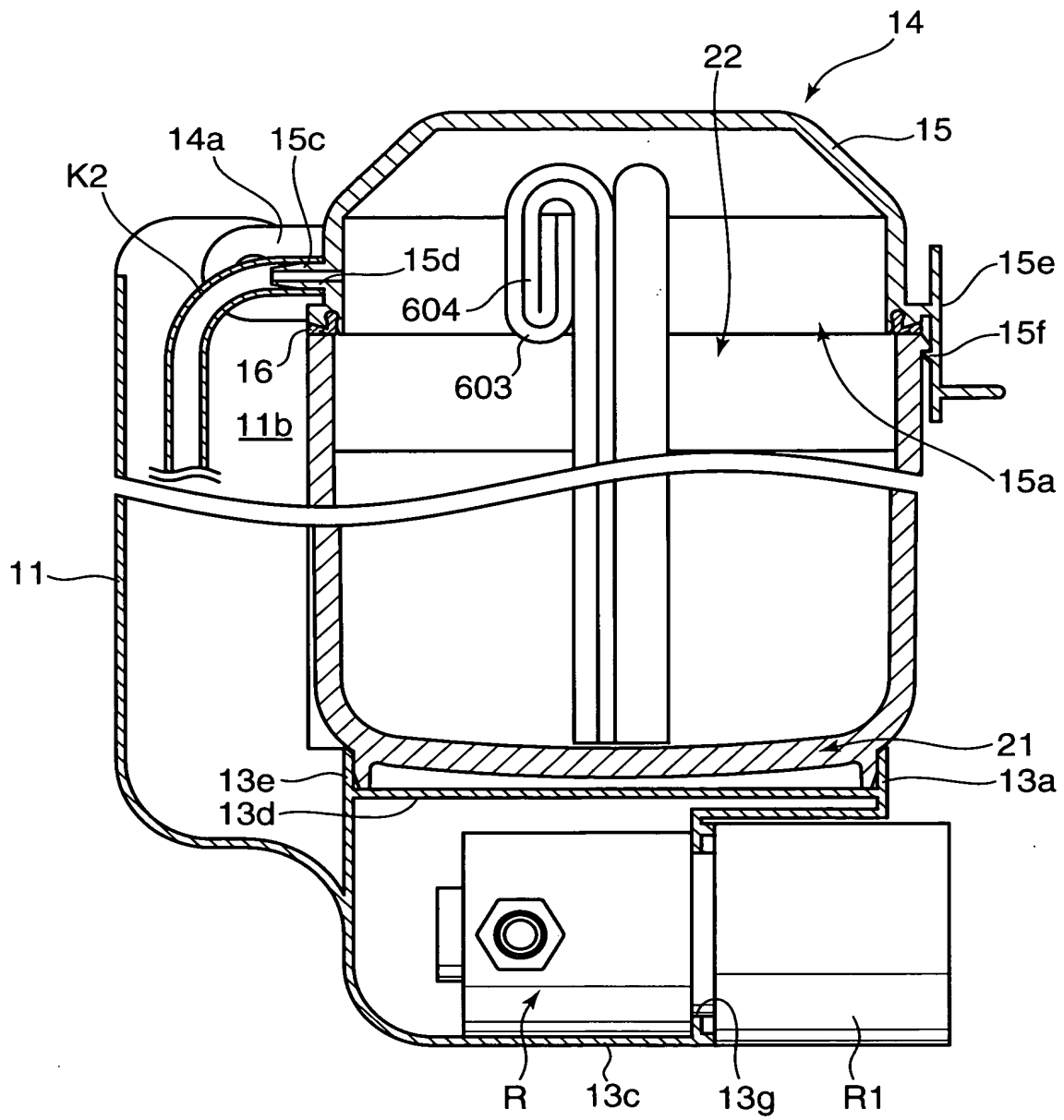


FIG. 12

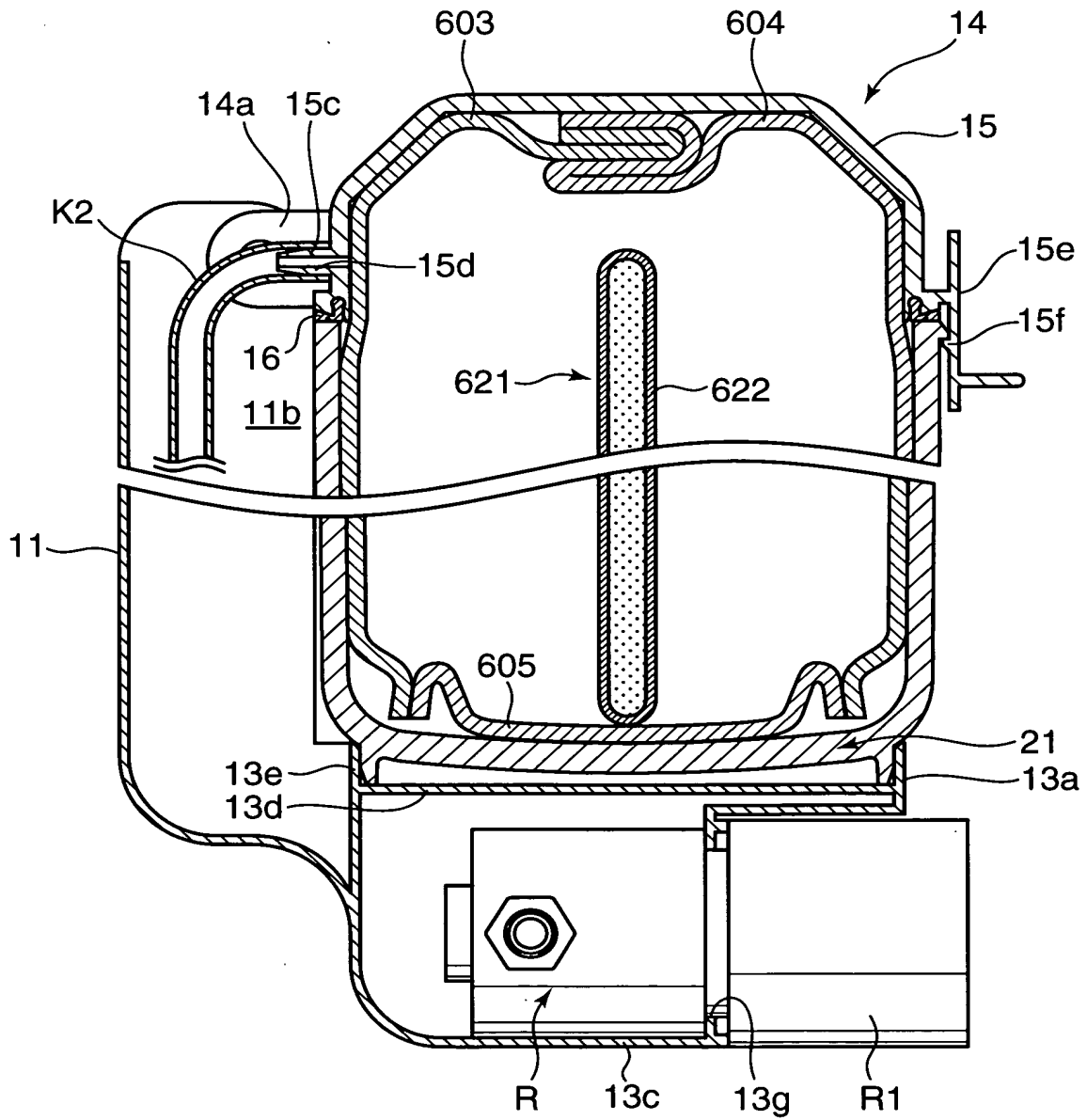


FIG. 13

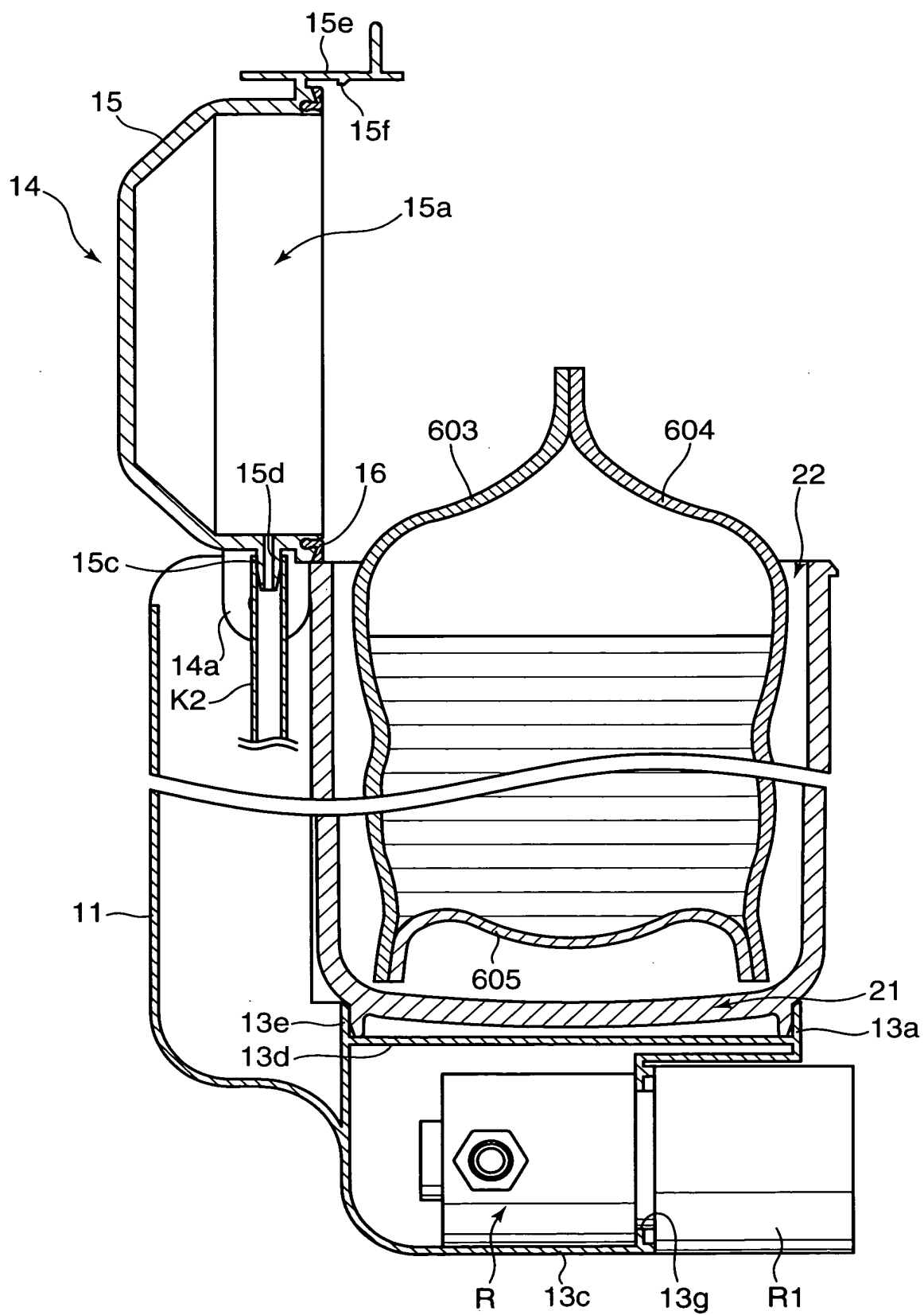


FIG. 14

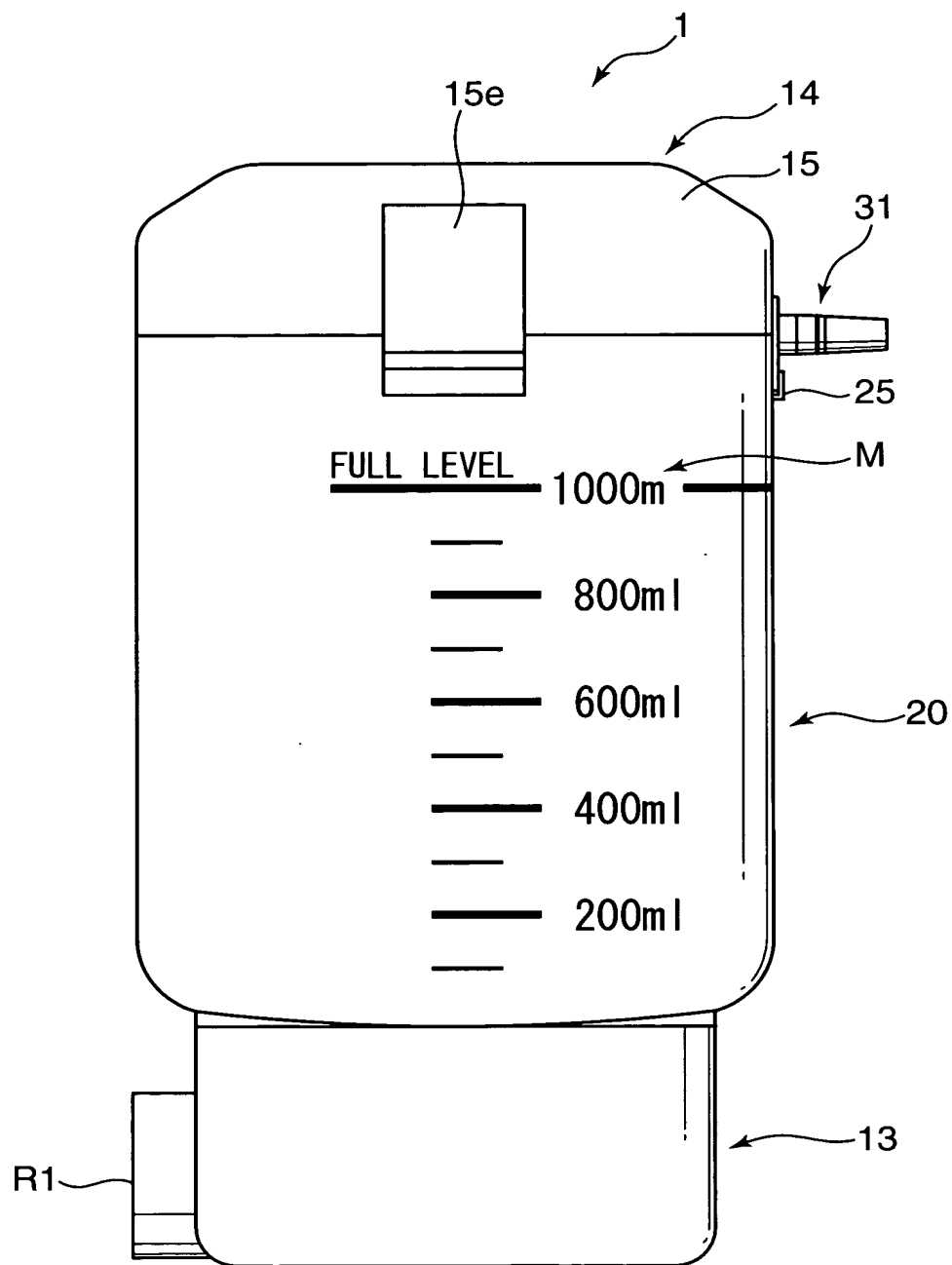


FIG. 15

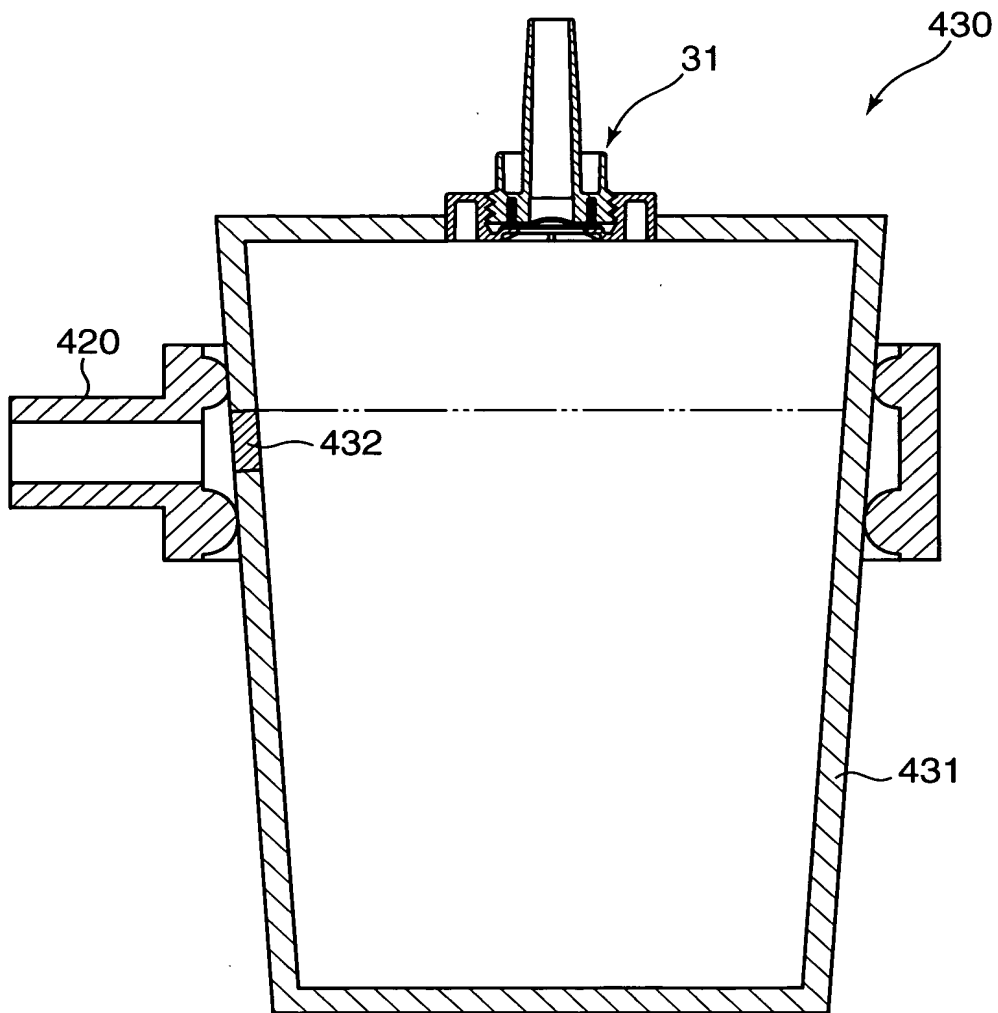


FIG. 16

